



This technology is currently not available for licensing

Tech ID: 30118

ADDITIONAL TECHNOLOGIES BY THESE INVENTORS

- ▶ Bonding of Heterogeneous Material for Improved Yield and Performance of Photonic Integrated Circuits
- ▶ Epitaxial Laser Integration on Silicon Based Substrates
- ▶ Vertical Cavity Surface-Emitting Lasers with Continuous Wave Operation
- ▶ Eliminating Misfit Dislocations with In-Situ Compliant Substrate Formation
- ▶ III-Nitride-Based Vertical Cavity Surface Emitting Laser (VCSEL) with a Dielectric P-Side Lens
- ▶ Enhanced Light Extraction LED with a Tunnel Junction Contact Wafer Bonded to a Conductive Oxide
- ▶ Integrated Reconfigurable Circulator
- ▶ Ultraviolet Laser Diode on Nano-Porous AlGaN template
- ▶ Improved Reliability & Enhanced Performance of III-Nitride Tunnel Junction Optoelectronic Devices
- ▶ Magneto-Optic Modulator
- ▶ Quantum Dot Photonic Integrated Circuits
- ▶ (In,Ga,Al)N Optoelectronic Devices with Thicker Active Layers for Improved Performance
- ▶ Method For The Removal Of Devices Using The Trench
- ▶ Thermally Stable, Laser-Driven White Lighting Device
- ▶ Integrated Dielectric Waveguide and Semiconductor Layer
- ▶ Orthogonal Mode Laser Gyro
- ▶ Methods for Fabricating III-Nitride Tunnel Junction Devices
- ▶ Contact Architectures for Tunnel Junction Devices
- ▶ III-Nitride Tunnel Junction LED with High Wall Plug Efficiency
- ▶ Novel Multilayer Structure for High-Efficiency UV and Far-UV Light-Emitting Devices
- ▶ A Method To Lift-Off Nitride Materials With Electrochemical Etch
- ▶ High-Intensity Solid State White Laser Diode
- ▶ Monolithically Integrated Laser-Nonlinear Photonic Devices
- ▶ Nitride Based Ultraviolet LED with an Ultraviolet Transparent Contact
- ▶ Misfit Dislocation Free Quantum Dot Lasers
- ▶ High-Efficiency and High-Power III-Nitride Devices Grown on or Above a Strain Relaxed Template
- ▶ III-Nitride Based VCSEL with Curved Mirror on P-Side of the Aperture

